

40V Dual N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

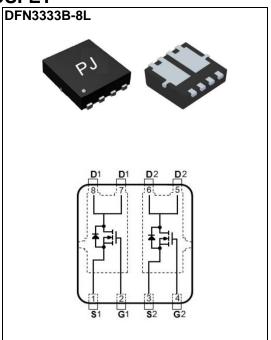
37 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@8A<15m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@6A<20m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultralow on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN3333B-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.001 ounces, 0.027 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	40	.,	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	37	А	
	T _C =100°C		23		
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	120		
Power Dissipation	T _C =25°C	Po	39.6	14/	
	Tc=100°C		19.8	W	
Continuous Drain Current	T _A =25°C	l _D	9		
	T _A =70°C		7	Α	
Power Dissipation	T _A =25°C	Po	2.4		
	T _A =70°C		1.6	W	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~175	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	Rejc	3.79	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =250uA	1.0	1.75	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =8A	-	12.5	15	mΩ
		V _{GS} =4.5V,I _D =6A	-	15.5	20	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V _{DS} =20V, I _D =10A, V _{GS} =4.5V (Note 2,3)	-	10	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	
Gate-Drain Charge	Q_{gd}		-	3.6	-	
Input Capacitance	Ciss	V _{DS} =20V, V _{GS} =0V,	-	1040	-	pF
Output Capacitance	Coss		-	117	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	84	-	
Turn-On Delay Time	td _(on)	$V_{DS}\text{==}20\text{V, }I_{D}\text{=}1\text{A,}$ $V_{GS}\text{==}10\text{V, }R_{G}\text{=}6\Omega$ (Note 2,3)	-	9.4	-	
Turn-On Rise Time	t _r		-	19	-	ns
Turn-Off Delay Time	td _(off)		-	66	-	
Turn-Off Fall Time	t _f		-	67	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	37	А
Diode Forward Current	ls					
Diode Forward Voltage	V _{SD}	I _S =1A,V _{GS} =0V	-	0.7	1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

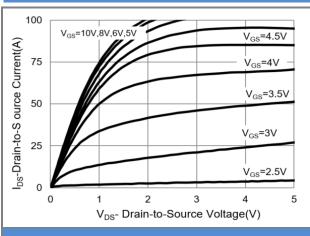


Fig.1 On-Region Characteristics

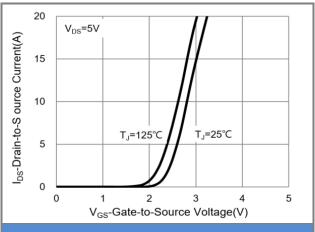


Fig.2 Transfer Characteristics

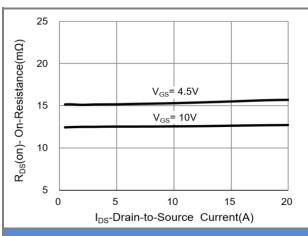


Fig.3 On-Resistance vs. Drain Current

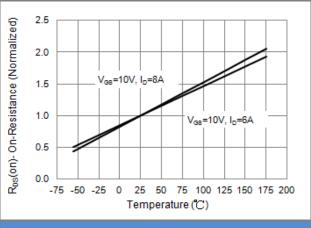
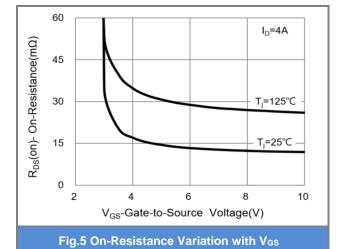


Fig.4 On-Resistance vs. Junction temperature



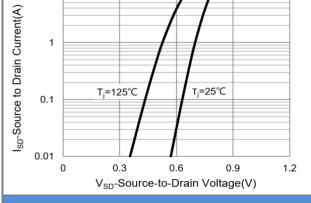


Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

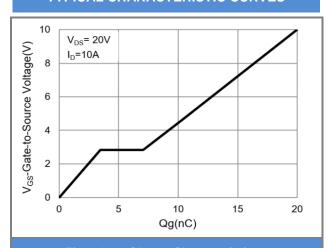


Fig.7 Gate-Charge Characteristics

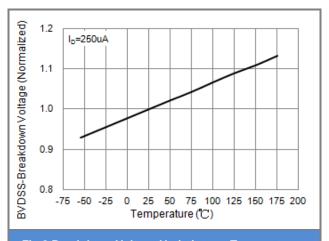


Fig.8 Breakdown Voltage Variation vs. Temperature

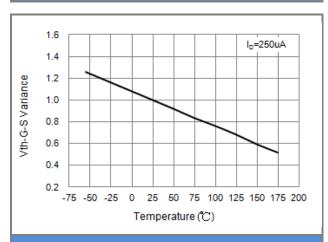


Fig.9 Threshold Voltage Variation with Temperature

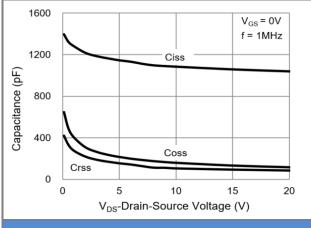
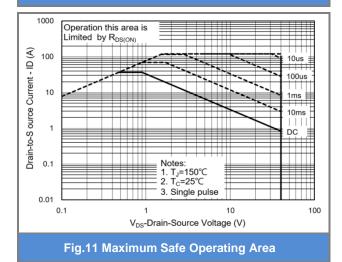


Fig.10 Capacitance vs. Drain-Source Voltage



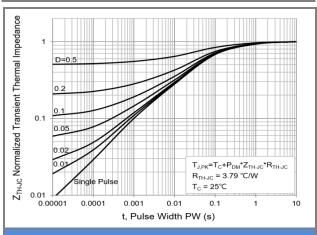


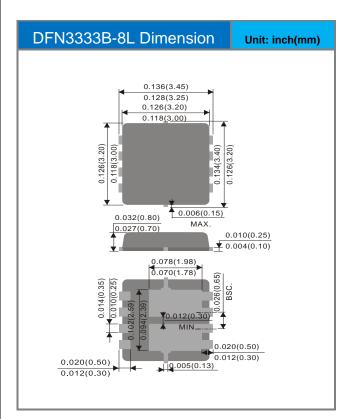
Fig.12 Normalized Transient Thermal Impedance

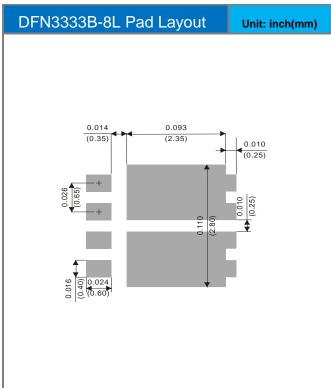


Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ4848P-AU	DFN3333B-8L	5K pcs / 13" reel	4848

Packaging Information & Mounting Pad Layout







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